
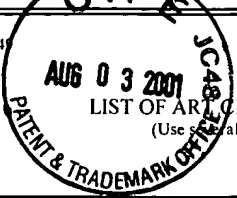


200. Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1035	SERIAL NO. 09/234,233	
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				FILING DATE January 20, 1999		
U.S. PATENT DOCUMENTS						
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
DV	AA	5,883,011	4/1999	Lin et al		
	AB	5,677,015	10/1994	Hasegawa		
	AC	5,783,493	7/1998	Yeh et al		
	AD	5,807,660	9/1998	Lin et al		
	AE	4,833,096	5/1989	Huang et al		
	AF	5,405,489	4/1995	Kim et al		
	AG	5,470,772	11/1995	Woo		
	AH	5,652,187	7/1997	Kim et al		
	AI	5,656,337	8/1997	Park et al		
	AJ	4,805,683	2/1989	Magdo et al		
	AK	5,874,367	2/1999	Dobson		
DV	AL					
FOREIGN PATENT DOCUMENTS						
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DV	AM	06067019A	9/1999	Japan (Glass)		
DV	AN	9750993	2/1997	Japan		
DV	AO	63-157443A	6/30/1988	Japan (Morita)		
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)						
DV	AP		TEXT: Jenkins, F. et al., "Fundamentals of Optics", Properties of Light, pp. 9-10. (No date)			
DV	AQ		TEXT: Wolf, S. et al., "Silicon Processing for the VLSI Era", Vol. 1, pp. 437-441. (No date)			
	AR					
EXAMINER			DATE CONSIDERED			
S. Muland			10/11/01			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.						

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	AB	5,219,613	6/1993	Fabry et al				
	AC	5,270,267	12/1993	Quellet				
	AD	5,541,445	7/1996	Quellet				
	AE	6,022,404	2/2000	Ettlinger et al				
	AF	5,709,741	1/1998	Akamastu et al				
	AG	4,648,904	3/1987	Depasquale et al				
	AH	4,158,717	6/1979	Nelson				
	AI	5,667,015	9/1997	Harestad et al				
	AJ	5,661,093	8/1997	Ravi et al				
	AK	5,536,857	7/1996	Naula				
	AL	4,695,859	9/1987	Guha et al				
	AM	4,954,867	6/1990	Hosaka				
	AN	5,441,797	8/1995	Hogan				
	AO	5,710,067	1/1998	Foote				
	AP	5,759,755	6/1998	Park et al				
	AQ	5,838,052	11/1998	McTeer				
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DV	AS	406244172A	9/1994	Japan				
DV	AT	593,727	10/1947	GB				
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<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>								

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. M122-1035		SERIAL NO. 09/234,233	
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*Examiner Initial	Class	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
DV	AA	5,061,509	10/1991	Naito et al				
	AB	4,600,671	7/1986	Saitoh et al				
	AC	5,753,320	5/1998	Mikoshiba et al				
	AD	5,356,515	10/1994	Tahara et al				
	AE	5,674,356	10/07/97	Nagayama				
	AF	5,731,242	03/24/98	Parat et al.				
	AG	5,741,721	04/21/98	Stevens				
	AH	5,034,348	07/23/91	Hartswick et al.				
	AI	5,472,829	12/05/95	Ogawa				
	AJ	5,641,607	06/24/97	Ogawa et al.				
DV	AK	5,648,202	07/15/97	Ogawa et al.				
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DV	AM	5-263255	10/1993	Japan				
DV	AN	0 471 185 A2	7/10/91	EPO				
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
DV	AO		D.R. McKenzie et al., "New Technology for PACVD", Surface and Coatings Technology, 82 (1996), pp. 326-333.					
DV	AP		S. McClatchie et al.; "Low Dielectric Constant Flowfill® Technology For IMD Applications"; undated; 7 pages					
DV	AQ		K. Beekmann et al.; "Sub-micron Gap Fill and In-Situ Planarisation using Flowfill™ Technology"; October 1995; pp. 1-7					
EXAMINER				DATE CONSIDERED				
S. Muland				10/11/01				
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Form PTO-144		 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1035		SERIAL NO. 09/234,233	
LIST OF ARTS CITED BY APPLICANT (Use separate sheets if necessary)				APPLICANT Weimin Li		FILING DATE January 20, 1999	
				GROUP 2818			

U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
DV	AA	5,670,297	09/23/97	Ogawa et al.			
	AB	5,677,111	10/14/97	Ogawa			
	AC	5,698,352	12/16/97	Ogawa et al.			
	AD	5,831,321	11/03/98	Nagayama			
	AE	5,591,566	01/07/97	Ogawa			
	AF	6,008,124	12/28/99	Sekiguchi et al.			
	AG	5,340,621	08/23/94	Matsumoto et al.			
	AH	5,600,165	02/04/97	Tsukamoto et al.			
	AI	5,872,385	02/16/99	Taft et al.			
	AJ	5,960,289	09/28/99	Tsui et al.			
	AK	5,968,324	10/19/99	Cheung et al.			
DV	AL	6,020,243	02/01/00	Wallace et al.			

FOREIGN PATENT DOCUMENTS							
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DV	AM	0 588 087 A2	8/18/93	EPO			
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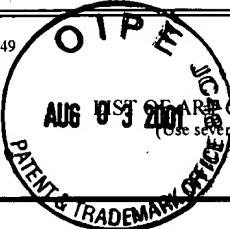
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)			
DV	AO		A. Kiermasz et al.; "Planarisation for Sub-Micron Devices Utilising a New Chemistry"; Electrotech, February 1995; 2 pages
DV	AP		IBM Technical Disclosure Bulletin "Low-Temperature Deposition of SiO <sub>2</sub> , Si <sub>3</sub> N <sub>4</sub> or SiO <sub>2</sub> -Si <sub>3</sub> N <sub>4</sub> ," Vol. 28, No. 9, p. 4170, Feb. 1986.
DV	AQ		ARTICLE: Bencher, C. et al., "Dielectric antireflective coatings for DUV lithography", Solid State Technology (March 1997), pp.109-114.

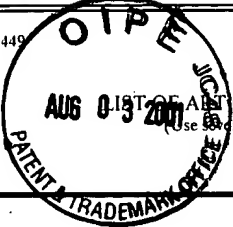
  


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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-1035		SERIAL NO. 09/234,233	
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					FILING DATE January 20, 1999			
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DV	AA	6,054,379	04/25/00	Yau et al.				
	AB	5,948,482	09/07/99	Brinker et al.				
	AC	5,800,877	09/01/98	Maeda et al.				
	AD	5,260,600	11/09/93	Harada				
	AE	4,992,306	02/12/91	Hochberg et al.				
	AF	4,702,936	10/27/87	Maeda et al.				
	AG	4,863,755	09/05/89	Hess et al.				
	AH	5,234,869	08/10/93	Mikata et al.				
	AI	5,302,366	04/12/94	Schuetz et al.				
	AJ	5,591,494	01/07/97	Sato et al.				
	AK	5,968,611	10/19/99	Kaloyeros et al.				
	AL	6,159,871	12/12/00	Loboda et al.				
	AM	5,744,399	4/1998	Rostoker				
	AN	5,883,014	3/1999	Chen				
DV	AO	6,017,779	1/25/00	Miyasaka				
FOREIGN PATENT DOCUMENTS								
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DV	AP	09055351	25/2/97	Japan				
DV	AQ	0 778 496 A2	05/12/96	EPO				
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
DV	AR	Noboru Shibata, "Plasma-Chemical Vapor-Deposited Silicon Oxide/Silicon Oxynitride Double-Layer Antireflective Coating for Solar Cells", Japanese Journal of Applied Physics, Vol. 30, No. 5, May 1991, pp. 997-1001.						
DV	AS	Julius Grant, Hack's Chemical Dictionary, Fourth Edition, McGraw-Hill Book Company, © 1969, rented by Grant © 1972, pp. 27						
EXAMINER <i>Stuland</i>				DATE CONSIDERED <i>10/11/01</i>				
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DV	AA	5,472,827	12/1995	Ogawa et al.				
	AB	6,156,674	12/5/00	Li et al				
	AC	6,461,003	10/24/95	Haveman				
	AD	6,124,641	9/26/00	Matsura				
	AE	5,554,567	9/10/96	Wang				
DV	AF	6,028,015	2/22/00	Wang				
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DV	AG	EP 0 464 515 A3/B1	08.01.92	EPO (Mikata et al.)				
DV	AH	EP 0 771 886 A1	07.05.97	EPO (Loboda)				
DV	AI	20029	US99	Search Report				
DV	AJ	20030	US99	Search Report				
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
DV	AK	Ralls, Kenneth M., "Introduction to Materials Science and Engineering", John Wiley & Sons, © 1976, pp. 312-313						
DV	AL	Ravi K. Laxan, "Synthesizing Low-k CVD Materials for Fab Use", Semiconductor International, Nov. 2000, 10 pps.						
DV	AM	Anonymous, "New gas helps make faster IC's, Machine Design Cleveland, © Penton Media, Inc., November 4, 1999, pp. 118						
DV	AN	Lobada et al, "Using Trimethylsilane to Improve Safety Throughput and Versatility in PECVD Processes", 4th International Symposium on Silicon Nitride and Silicon Dioxide Thin Insulating Films, The Electrochemical Society. Abstract No. 358, p. 454, May 1997.						
DV	AO	ARTICLE: Bencher, C. et al., "Dielectric antireflective coatings for DUV lithography", Solid State Technology (March 1997), pp. 109-114.						
DV	AP	ARTICLE: Dammel, R. R. et al., "Dependence of Optical Constants of AZ® BARLi™ Bottom Coating on Back Conditions", SPIE Vol. 3049 (1997), pp. 963-973.						
DV	AQ	TEXT: Heavens, O. S., "Optical Properties of Thin Solid Films", pp. 48-49.						
EXAMINER				DATE CONSIDERED				
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<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>								

Form PTO-1449		 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-1035		SERIAL NO. 09/234,233	
LIST OF ART CITED BY APPLICANT AUG 03 2001 (Use additional sheets if necessary)					APPLICANT Weimin Li			
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DV	AA	09/146,842	9/3/98	Yin et al				
DV	AB	09/146,843	9/3/98	Li et al				
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## U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
DV	AA	4,474,975	10/84	Clemons et al.			
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## FOREIGN PATENT DOCUMENTS

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							Yes	No
	AL							
	AM							
	AN							

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

DV	AO		M. Matsuura et al.; "A Highly Reliable Self-planarizing Low-k Intermetal Dielectric for Sub-quarter Micron Interconnects"; July 1997;
			pp. 31.6.1-31.6.4
DV	AP		O. Horie et al.; "Kinetics and Mechanism of the Reactions of O <sub>2</sub> P with SiH <sub>4</sub> , CH <sub>3</sub> SiH <sub>3</sub> , (CH <sub>3</sub> ) <sub>2</sub> SiH <sub>2</sub> , and (CH <sub>3</sub> ) <sub>3</sub> SiH"; The Journal of Physical Chemistry, Vol. 95, No. 11, 1991; pp. 4393-4400
DV	AQ		Robert Withmall et al.; "Matrix Reactions of Methylsilanes and Oxygen Atoms"; The Journal of Physical Chemistry, Vol. 92, No. 3, 1988;
			pp. 594-602
DV	AR		Ajei M. Joshi et al.; "Plasma Deposited Organosilicon Hydride Network Polymers as Versatile Resists for Entirely Dry Mid-Deep UV Photolithography"; SPIE Vol. 1925, 1993; pp. 709-720

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200.FORM PTO-101

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
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09/234,233LIST OF ART CITED BY APPLICANT  
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January 20, 1999GROUP  
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## U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
DV	AA	5,314,724	05/1994	Tsukane et al			
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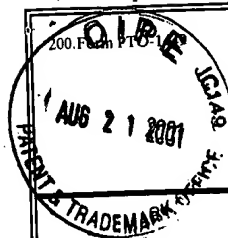
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PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO.  
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Weimin Li

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U.S. PATENT DOCUMENTS

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	AD	6,072,227	06/2000	Yau et al			
	AE	5,786,039	7/1998	Brouquet			
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